



# **FQU13N10LTU Information**



For Reference Only

Part Number FQU13N10LTU

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 100V 10A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **FQU13N10LTU Specifications**

Manufacturer         FQU13N10LTU           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-251-3 Short Leads, IPak, TO-251AA           Series         QFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         10A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         5V, 10V           Vgs(th) (Max) @ Id         2V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         12nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         520pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2.5W (Ta), 40W (Tc)           Rds On (Max) @ Id, Vgs         180 mOhm @ 5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole		
CategoryDiscrete Semiconductor ProductsPackageTo-251-3 Short Leads, IPak, TO-251AASeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds520pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 40W (Tc)Rds On (Max) @ Id, Vgs180 mohm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Manufacturer Part Number	FQU13N10LTU
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Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 12nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 520pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 40W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  100V  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  180 mOhm @ 5A, 10V  Operating Temperature  Mounting Type  N-Channel  100V  104  2V @ 250µ  5V, 10V  2V @ 250µA  12nC @ 5V  Input Capacitance (Ciss) (Max) @ Vds  520pF @ 25V  Ygs (Max)  ±20V  FET Feature	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds520pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 40W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Series	QFET?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Input Capacitance (Ciss) (Max) @ Vds  2.5W (Ta), 40W (Tc)  Rds On (Max) @ Id, Vgs  Input Capacitance (Ciss) (Max) @ Cite (Ciss) (Max) (Max)  Through Hole	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Ags On (Max) @ Id, Vgs  Departing Temperature  Poperating Temperature  Current - Continuous Drain (Id) @ 25°C  10A (Tc)  5V, 10V  2V @ 250μA  12nC @ 5V  12n	Technology	MOSFET (Metal Oxide)
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Vgs(th) (Max) @ Id       2V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       12nC @ 5V         Input Capacitance (Ciss) (Max) @ Vds       520pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       2.5W (Ta), 40W (Tc)         Rds On (Max) @ Id, Vgs       180 mOhm @ 5A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole	Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  520pF @ 25V  Vgs (Max)  #20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  180 mOhm @ 5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Drive Voltage (Max Rds On, Min Rds On)	5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  520pF @ 25V  Vgs (Max)  ET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  180 mOhm @ 5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Vgs(th) (Max) @ Id	2V @ 250μA
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Rds On (Max) @ Id, Vgs $180 \text{ mOhm } @ 5A, 10V$ Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C (TJ)}$ Mounting Type $\text{Through Hole}$	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$ Mounting Type Through Hole	Power Dissipation (Max)	2.5W (Ta), 40W (Tc)
Mounting Type Through Hole	Rds On (Max) @ Id, Vgs	180 mOhm @ 5A, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Supplier Davice Deakers	Mounting Type	Through Hole
Supplied Device Fackage 1-Fak	Supplier Device Package	I-Pak
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
Report errors?		Report errors?

## **FQU13N10LTU Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **FQU13N10LTU Payment Methods**

































If you have any question about FQU13N10LTU, please do not hesitate to contact us!

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